

# **isc Silicon NPN Power Transistor**

# 2SD1355

## DESCRIPTION

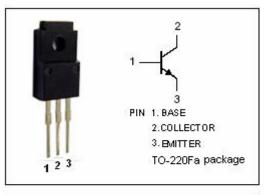
- Low Collector Saturation Voltage : V<sub>CE(sat)</sub>= 2.0V(Max)@ I<sub>C</sub>= 4A
- Collector-Emitter Breakdown Voltage-
  - : V<sub>(BR)CEO</sub>= 100V (Min)
- Complement to Type 2SB995
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

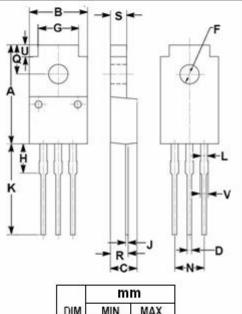
## **APPLICATIONS**

- Power amplifier applications.
- Recommended for 30W high-fidelity audio frequency amplifier output stage.

SYMBOL	PARAMETER	VALUE	UNIT
Vсво	Collector-Base Voltage	100	V
V <sub>CEO</sub>	Collector-Emitter Voltage	100	V
V <sub>EBO</sub>	Emitter-Base Voltage	5	V
lc	Collector Current-Continuous	5	A
I <sub>B</sub>	Base Current-Continuous	0.5	A
Pc	Collector Power Dissipation @ $T_c=25^{\circ}C$	40	W
TJ	Junction Temperature	150	°C
T <sub>stg</sub>	Storage Temperature Range	-55~150	°C

### ABSOLUTE MAXIMUM RATINGS(T<sub>a</sub>=25°C)





DIM	MIN	MAX
Α	16.85	17.15
В	9.54	10.10
С	4.35	4.65
D	0.75	0.90
F	3.20	3.40
G	6.90	7.20
Н	3.80	4.20
J	0.45	0.75
Κ	13.35	13.80
L	1.10	1.30
N	4.98	5.18
Q	4.85	5.15
R	2.55	3.25
S	2.70	2.90
U	1.75	2.05
V	1.30	1.50

isc website: www.iscsemi.com



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# **ELECTRICAL CHARACTERISTICS**

#### $T_c=25^{\circ}C$ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	МАХ	UNIT
V <sub>(BR)CEO</sub>	Collector-Emitter Breakdown Voltage	I <sub>C</sub> = 10mA; I <sub>B</sub> = 0	100			V
V <sub>CE(sat)</sub>	Collector-Emitter Saturation Voltage	I <sub>C</sub> = 4A; I <sub>B</sub> = 0.4A			2.0	V
V <sub>BE</sub> (on)	Base-Emitter On Voltage	I <sub>C</sub> = 1A; V <sub>CE</sub> = 5V			1.5	V
I <sub>CBO</sub>	Collector Cutoff Current	V <sub>CB</sub> = 100V; I <sub>E</sub> = 0			100	μ Α
I <sub>EBO</sub>	Emitter Cutoff Current	V <sub>EB</sub> = 5V; I <sub>C</sub> = 0			100	μ Α
hfe-1	DC Current Gain	Ic= 1A; Vce= 5V	40		240	
h <sub>FE-2</sub>	DC Current Gain	I <sub>C</sub> = 4A; V <sub>CE</sub> = 5V	20			
f <sub>T</sub>	Current-Gain—Bandwidth Product	I <sub>C</sub> = 1A; V <sub>CE</sub> = 5V		12		MHz
Сов	Output Capacitance	I <sub>E</sub> = 0; V <sub>CB</sub> = 10V; f <sub>test</sub> = 1MHz		100		pF

#### h<sub>FE-1</sub> Classifications

R	0	Y
40-80	70-140	120-240

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